

Customer No.: 31561  
Application No.: 10/710,637  
Docket No.: 11514-US-PA

### AMENDMENTS

Please amend the application as indicated hereafter.

#### To the Claims :

1. (original) A method of forming an overlay mark, comprising:
  - forming a first material layer on a substrate;
  - forming a first trench serving as a first portion of a trench type outer mark in the first material layer;
  - forming a first deposition layer on the first material layer, wherein the first trench is partially or incompletely filled with the first deposition layer;
  - performing a first chemical mechanical polishing process on the first deposition layer until the first material layer is exposed leaving a remaining portion of the first deposition layer in the first trench;
  - forming a second material layer to cover the first material layer and the first deposition layer, wherein a thickness of the second material layer is smaller than that of the first material layer;
  - removing the second material layer on the trench type outer mark to form a second trench exposing at least a portion of the first deposition layer in the first trench, wherein the second trench serves as a second portion of the trench type outer mark;
  - forming a second deposition layer on the substrate to cover the second material layer and the first deposition layer in the first trench;
  - performing a second chemical mechanical polishing process on the second

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deposition layer until the second material layer in the second trench is exposed; forming a third deposition layer on the second material layer, wherein a step height is formed on the third deposition layer between the edge of the first trench and the center of the first trench; and

forming a raised feature serving as an inner mark on the third deposition layer.

2. (original) The method of claim 1, wherein a width of the second trench is larger than that of the first trench, and the second trench exposes the first deposition layer in the first trench and a portion of the first material layer.

3. (original) The method of claim 2, wherein a difference in distance between a side wall of the second trench and that of the first trench is no less than 150 nm.

4. (original) The method of claim 1, wherein a width of the second trench is smaller than that of the first trench and the second trench exposes a portion of the first deposition layer in the first trench.

5. (original) The method of claim 1, wherein the raised feature comprises a patterned photoresist layer.

6. (original) The method of claim 1, wherein the first material layer and the second material layer comprise a dielectric layer respectively, and the first deposition layer, the second deposition layer and the third deposition layer comprise a metal layer respectively.

7. (original) A method of forming an overlay mark, comprising:  
forming a first material layer on a substrate;  
 patterning the first material layer to form a first raised feature serving as a portion of a raised type outer mark on the substrate;

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forming a first deposition layer to cover the substrate and the first raised feature, wherein a thickness of the first deposition layer is thinner than that of the first material layer;

performing a first chemical mechanical polishing process on the first deposition layer until a top surface of the first raised feature is exposed;

forming a second material layer to cover the first deposition layer and the first raised feature, wherein a thickness of the second material layer is smaller than that of the first material layer;

patterning the second material layer to form a second raised feature on the first raised feature serving as the other portion of the raised type outer mark on the substrate;

forming a second deposition layer to cover the second raised feature and the first deposition layer;

performing a second chemical mechanical polishing process on the second deposition layer until a top surface of the second raised feature is exposed;

forming a third deposition layer on the second material layer, wherein a step height is formed on the third deposition layer between the edge of the second raised feature and the center of the second raised feature; and

forming a third raised feature serving as an inner mark layer on the third deposition layer.

8. (original) The method of claim 7, wherein a width of the second raised feature is smaller than that of the first raised feature, so that the second raised feature exposes a portion of the first raised feature.

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9. (original) The method of claim 8, wherein a difference in distance between a side wall of the first raised feature and that of the second raised feature is no less than 150 nm.

10. (original) The method of claim 7, wherein a width of the second raised feature is larger than that of the first raised feature, so that the second raised feature covers the first raised feature and a portion of the first deposition layer.

11. (original) The method of claim 7, wherein the third raised feature comprises a patterned photoresist layer.

12. (original) The method of claim 7, wherein the first material layer and the second material layer comprise a dielectric layer respectively, and the first deposition layer, the second deposition layer and the third deposition layer comprise a metal layer respectively.

Claims 13-23. (cancelled)